

Improved Efficiency GaN-based Light Emitting Devices ABSTRACT

- 5 An optical semiconductor device having an active layer for generating light via the recombination of holes and electrons therein. The active layer is part of a plurality of semiconductor layers including an n-p junction between an n-type layer and a p-type layer. The active layer has a polarization field therein having a field direction that depends on the orientation of the active layer when the active layer is grown. In the present invention, the
- 10 polarization field in the active layer has an orientation such that the polarization field is directed from the n-layer to the p-layer.

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